

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device according to this invention is characterized by including the steps of a) forming, on one major surface of a substrate, a gate structure constituted by either one of a dummy gate electrode and a gate electrode having an insulating film at least on bottom surface, and a device isolation insulating film so as to form a first groove divided by the dummy gate electrode or the gate electrode, to position the dummy gate electrode or the gate electrode in the first groove, and to form the gate structure to have an upper surface level not higher than an upper level of the device isolation insulating film, and b) forming source and drain electrodes in the first groove.

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